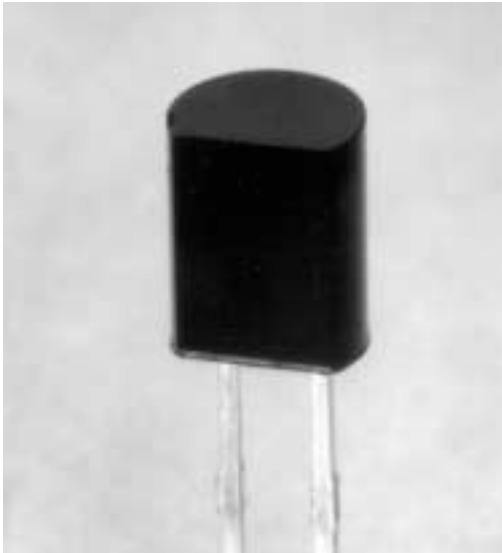
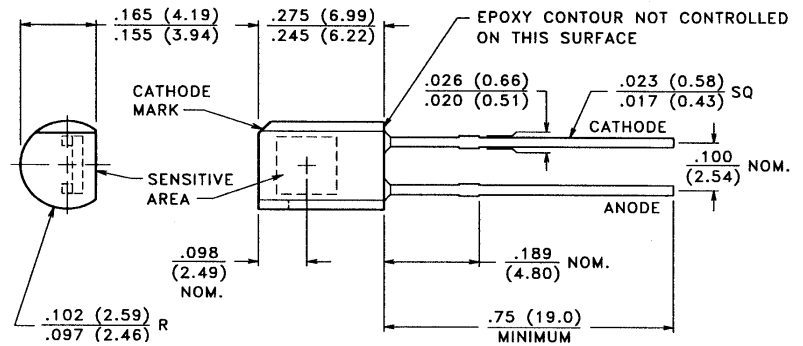


# Alternate Source/ Second Source Photodiodes

# VTD206H (SFH206 INDUSTRY EQUIVALENT)



## PACKAGE DIMENSIONS inch (mm)



CASE 61 TO-92 TYPE (FLAT LENS)  
CHIP ACTIVE AREA: .011 in<sup>2</sup> (7.41 mm<sup>2</sup>)

## PRODUCT DESCRIPTION

Large area planar silicon photodiode in a cast epoxy sidelooker, similar in outline to the TO-92 package. The package material filters out all visible light but passes infrared. These diodes exhibit low dark current under reverse bias and fast speed of response.

## ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -40°C to 100°C  
Operating Temperature: -40°C to 100°C

## RoHS Compliant



## ELECTRO-OPTICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTD206H			UNITS
			Min.	Typ.	Max.	
$I_{SC}$	Short Circuit Current	940 nm, H = 0.5 mW/cm <sup>2</sup>	15	25		μA
TC $I_{SC}$	$I_{SC}$ Temperature Coefficient	2856 K		.20		%/°C
$V_{OC}$	Open Circuit Voltage	940 nm, H = 0.5 mW/cm <sup>2</sup>	250	350		mV
TC $V_{OC}$	$V_{OC}$ Temperature Coefficient	2856 K		-2.6		mV/°C
$I_D$	Dark Current	H = 0, $V_R$ = 10 V		2	30	nA
$C_J$	Junction Capacitance	H = 0, $V_R$ = 0 V, 1 MHz		72		pF
$t_R/t_F$	Rise/Fall Time @ $R_L$ = 50Ω	$V_R$ = 5 V, 850 nm		20		nsec
$S_R$	Sensitivity	@ Peak		0.6		A/W
$\lambda_{range}$	Spectral Application Range		750		1100	nm
$\lambda_p$	Spectral Response - Peak			925		nm
$V_{BR}$	Breakdown Voltage		20	50		V
$\theta_{1/2}$	Angular Resp.-50% Resp. Pt.			±60		Degrees